



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

**H. WATANABE et al.**

Group Art Unit: 2825

Serial No.: 09/320,271

Examiner: C. Lee

Filed: May 27, 1999

For: **SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF**

**PRELIMINARY AMENDMENT**

Commission for Patents  
Washington, D. C. 20231

January 28, 2002

Sir:

Prior to continued examination on the merits, please amend the above- identified application  
as follows:

**IN THE CLAIMS:**

**Please amend claim 1 as follows:**

1. **(Three Times Amended)** A fabrication method of a semiconductor device  
comprising the steps of:
- forming a first insulation layer over a substrate,
  - introducing impurities into said first insulation layer,
  - forming, in said first insulation layer, a trench extending in a line, and
  - embedding and forming a first conductive layer in said trench extending linearly.